

**Amplifier, Power, 1.2W  
5.7-8.5 GHz**

**MAAP-000068-PKG003**  
Rev —  
Advance Datasheet

**Features**

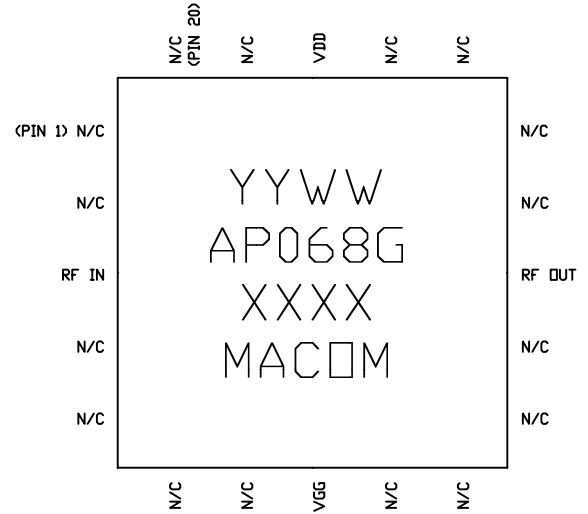
- ◆ **1.2 Watt Saturated Output Power Level**
- ◆ **Variable Drain Voltage (4-10V) Operation**
- ◆ **MSAG™ Process**

**Description**

The MAAP-000068-PKG003 is a 3-stage 1.2 W power amplifier with on-chip bias networks in a 20 lead, 5 mm PQFN package, allowing easy assembly. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Each device is 100% RF tested to ensure performance compliance. The part is fabricated using M/A-COM's GaAs Multifunction Self-Aligned Gate (MSAG) Process.

The 5 mm PQFN package has a lead-free lead finish that is RoHS compliant and compatible with a 260°C reflow temperature. The package also features low lead inductance and an excellent thermal path. The MTTF is 1,000,000 hours at 170°C.



**Primary Applications**

- ◆ **Point-to-Point Radio**
  - ◇ **6, 7, and 8 GHz Bands**
- ◆ **SatCom**
- ◆ **Broadband Wireless Access**

**Electrical Characteristics:  $T_c = 35^\circ C^1$ ,  $Z_0 = 50 \Omega$ ,  $V_{DD} = 8V$ ,  $I_{DQ} = 320mA^2$ ,  $P_{in} = 8dBm$ ,  $R_G = 60\Omega$**

Parameter	Symbol	Typical	Units
Bandwidth	f	5.7-8.5	GHz
Output Power	$P_{OUT}$	31	dBm
1-dB Compression Point	$P_{1dB}$	30	dBm
Small Signal Gain	G	25	dB
Input VSWR	VSWR	1.6:1	
Output VSWR	VSWR	2.5:1	
Output Third Order Intercept	TOI	38	dBm
Output Third Order Intermod, $P_{out} = 24 \text{ dBm (DCL)}$	IMD3	35	dBc
Gate Current	$I_{GG}$	5	mA
Drain Current	$I_{DD}$	470	mA

1.  $T_c$  = Case Temperature
2. Adjust  $V_{GG}$  between -2.6 and -1.2V to achieve specified  $I_{dq}$ .

### Maximum Operating Conditions <sup>3</sup>

Parameter	Symbol	Absolute Maximum	Units
Input Power	P <sub>IN</sub>	13.0	dBm
Drain Supply Voltage	V <sub>DD</sub>	+12.0	V
Gate Supply Voltage	V <sub>GG</sub>	-3.0	V
Quiescent Drain Current (No RF)	I <sub>DQ</sub>	520	mA
Quiescent DC Power Dissipated (No RF)	P <sub>DISS</sub>	5.2	W
Junction Temperature	T <sub>J</sub>	170	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

3. Operation beyond these limits may result in permanent damage to the part.

### Recommended Operating Conditions<sup>4</sup>

Characteristic	Symbol	Min	Typ	Max	Unit
Drain Voltage	V <sub>DD</sub>	4.0	8.0	8.0	V
Gate Voltage	V <sub>GG</sub>	-2.6	-2.0	-1.2	V
Input Power	P <sub>IN</sub>		8.0	11.0	dBm
Thermal Resistance	Θ <sub>JC</sub>		32		°C/W
Case Temperature	T <sub>C</sub>			Note 4	°C

4. Operation outside of these ranges may reduce product reliability.

5. Case Temperature = 170°C — Θ<sub>JC</sub> \* V<sub>DD</sub> \* I<sub>DQ</sub>

### Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

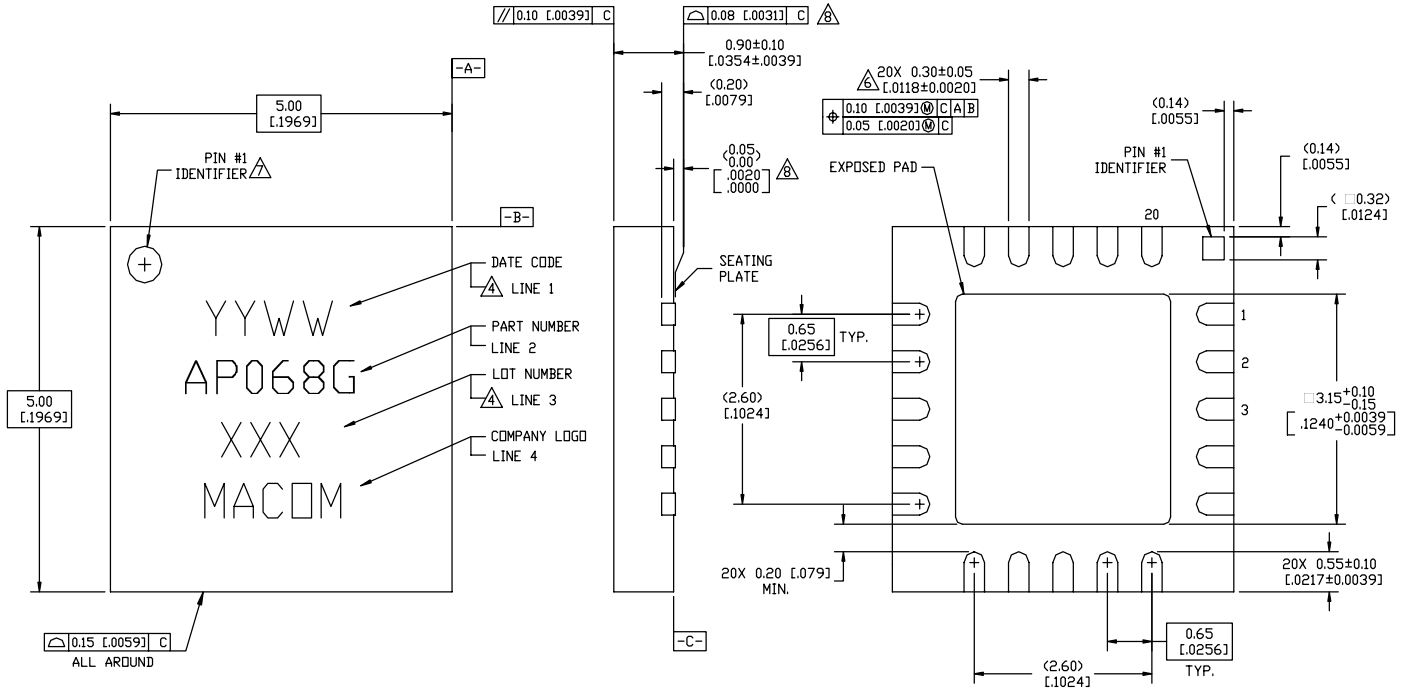
1. Apply V<sub>GG</sub> = -2 V, V<sub>DD</sub> = 0 V.
2. Ramp V<sub>DD</sub> to desired voltage, typically 8.0 V.
3. Adjust V<sub>GG</sub> to set I<sub>DQ</sub>, (approximately @ -2 V).
4. Set RF input.
5. Power down sequence in reverse. Turn V<sub>GG</sub> off last.



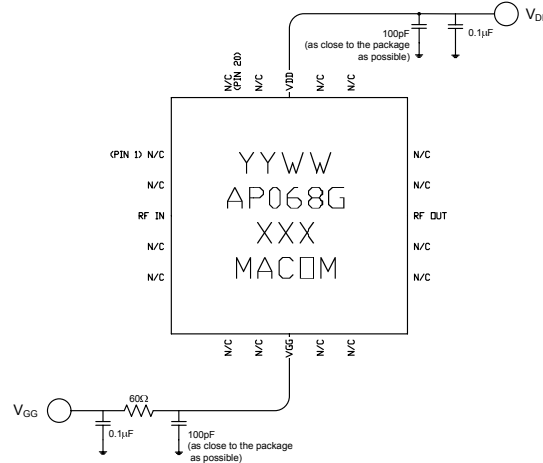
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**Figure 1. 5x5 mm 20-Lead MLP.**



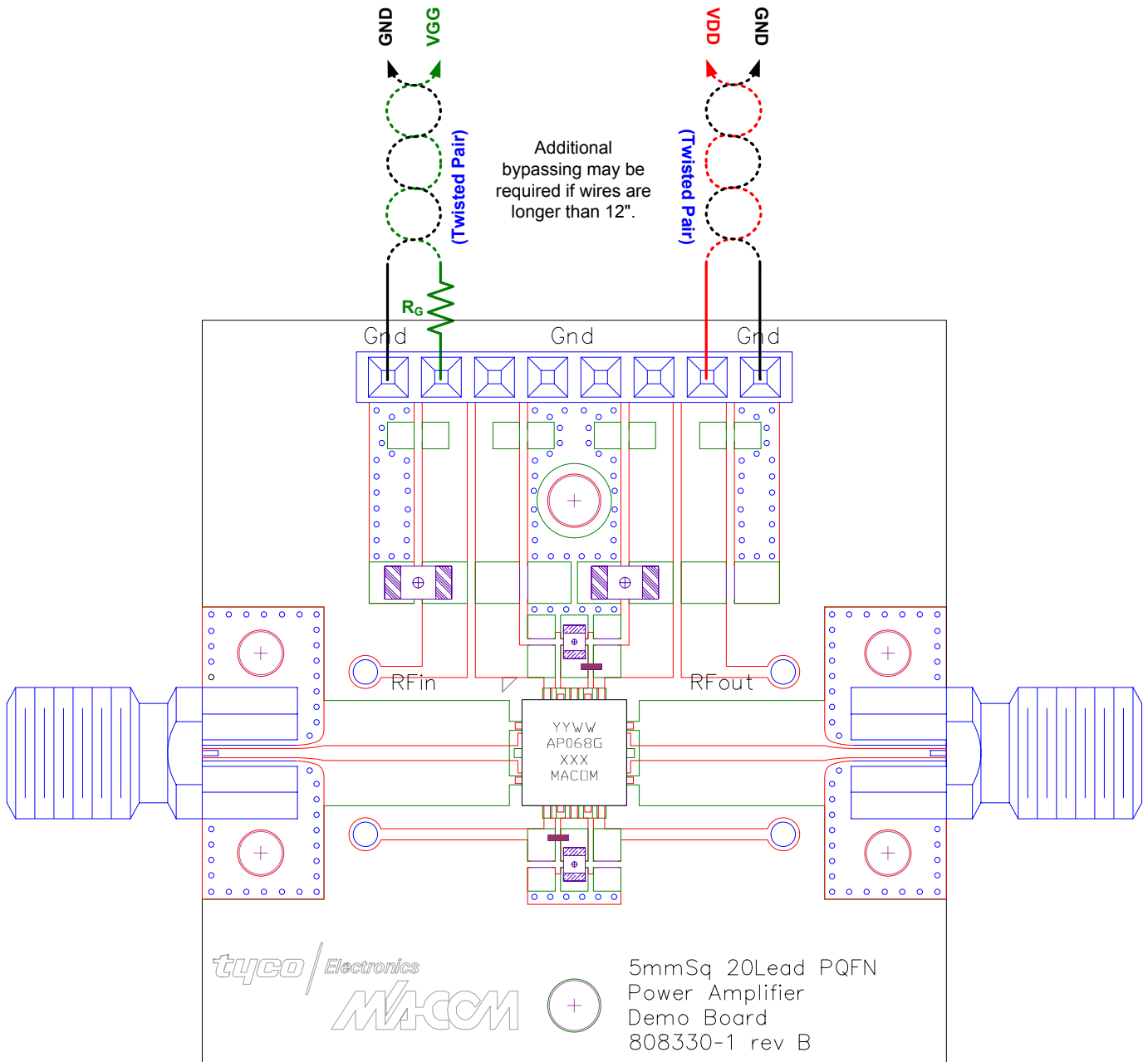
**Figure 2. Recommended Bias Configuration.**

Note: The exposed pad centered on the package bottom must be connected to RF and dc ground for proper electrical and thermal operation.

Refer to M/A-COM Application Note **Surface Mounting Instructions for PQFN Packages #S2083\*** for assembly guidelines.

**Additional Precaution: All parts must receive a bake-out of 125°C for 24 hours prior to any solder reflow operation.**

\*Application Notes can be found by going to the Site Search Page of M/A-COM's web page (<http://www.macom.com/Application%20Notes/index.htm>) and searching for the required Application Note.



**Figure 3. Demonstration Board P/N MAAP-000068-SMB003 (available upon request).**